#### Numerical Simulation of Dynamic Systems: Hw12 - Solution

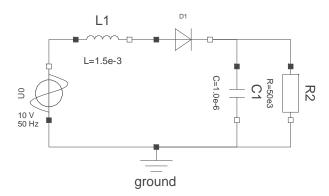
Prof. Dr. François E. Cellier
Department of Computer Science
FTH Zurich

May 28, 2013

└─Variable Structure System

#### [H9.14] Leaky Diode

#### Given the electrical circuit:



#### [H9.14] Leaky Diode II

We wish to simulate the circuit using the rkf45rt routine developed in homework problem [H9.1].

└Variable Structure System

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└Variable Structure System

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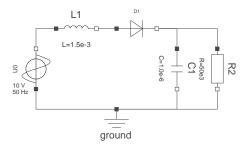
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- ▶ We shall be using the *leaky diode* approach to avoid the division by zero.
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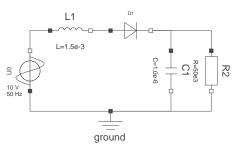
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- ► Repeat the simulation, but this time around, choose  $R_{on} = 10^{-5} Ω$  and  $G_{off} = 10^{-5} mho$ .

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- Repeat the simulation, but this time around, choose  $R_{on} = 10^{-5} Ω$  and  $G_{off} = 10^{-5} mho$ .
- Split the screen into two subgraphs, and plot in the top subgraph the voltages across the capacitor together from the two simulation runs, and on the bottom subgraph the step sizes used by the two simulation runs.
- What do you conclude?

└─Variable Structure System





1: 
$$U_0 = V_0 \cdot \sin(\frac{2\pi t}{t_p})$$
  
2:  $u_L = L_1 \cdot \frac{di_0}{dt}$   
3:  $i_C = C_1 \cdot \frac{dt_R}{dt}$   
4:  $u_R = R_2 \cdot i_R$ 

2: 
$$u_L = L_1 \cdot \frac{d}{dt}$$
  
3:  $i_C = C_1 \cdot \frac{du_R}{dt}$ 

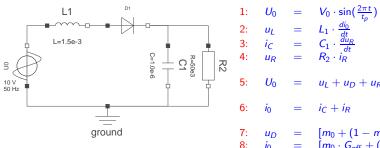
4: 
$$u_R = R_2 \cdot i_R$$

$$5: \quad U_0 = u_L + u_D + u_R$$

6: 
$$i_0 = i_C + i_R$$

7: 
$$u_D = [m_0 + (1 - m_0) \cdot R_{on}] \cdot s$$
  
8:  $i_0 = [m_0 \cdot G_{off} + (1 - m_0)] \cdot s$ 

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1: 
$$U_0 = V_0 \cdot \sin(\frac{2\pi t}{t_p})$$

2: 
$$u_L \equiv L_1 \cdot \frac{1}{dt}$$
  
3:  $i_C = C_1 \cdot \frac{du_R}{dt}$ 

4: 
$$u_R = R_2 \cdot i_R^{dt}$$

$$5: \quad U_0 = u_L + u_D + u_R$$

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 $m_0$  is a discrete state variable. It is *true*, when the diode is *blocking*.

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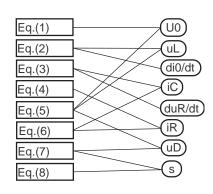
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$$\begin{array}{llll} \textbf{2:} & u_L & = & L_1 \cdot \frac{di_0}{dt} \\ \textbf{3:} & i_C & = & C_1 \cdot \frac{du_R}{dt} \\ \textbf{4:} & u_R & = & R_2 \cdot i_R \end{array}$$

3: 
$$i_C = C_1 \cdot \frac{du_R}{dt}$$

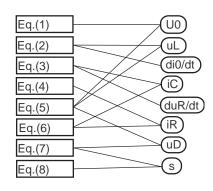
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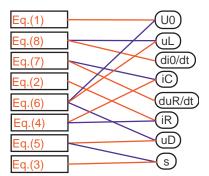
As expected, variable s does not show up inside an algebraic loop. It must be computed from the last equation.

└─Variable Structure System

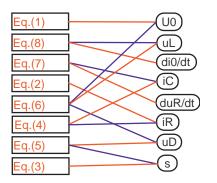
#### [H9.14] Leaky Diode V

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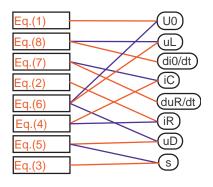


We causalize as much as we can:



1: 
$$U_0 = V_0 \cdot \sin(\frac{2\pi t}{t_p})$$
  
2:  $i_R = \frac{1}{R_2} \cdot u_R$   
3:  $s = \frac{1}{m_0 \cdot G_{off} + (1 - m_0)} \cdot i_0$   
4:  $i_C = i_0 - i_R$   
5:  $u_D = [m_0 + (1 - m_0) \cdot R_{on}] \cdot s$   
6:  $u_L = U_0 - u_D - u_R$   
7:  $\frac{du_R}{dt} = \frac{1}{C_1} \cdot i_C$   
8:  $\frac{di_0}{dt} = \frac{1}{L_1} \cdot u_L$ 

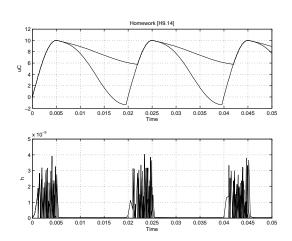
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8:  $\frac{di_0}{dt} = \frac{1}{L_1} \cdot u_L$ 

We were able to causalize all equations at once. The system feels like an *index-0* system. However with an ideal diode, we would be confronted with a *conditional index change*.

Variable Structure System



└Variable Structure System

## [H9.14] Leaky Diode VII

We notice that the simulation took forever. When the diode is blocking, an ideal diode would have led to a division by zero, whereas the leaky diode leads to an incredibly stiff model. We should have used a stiff system solver!

└─Variable Structure System

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- ▶ The simulation results look vastly different. Depending on the value of a fudge parameter that has no direct physical meaning, we got simulation trajectories that look significantly different.

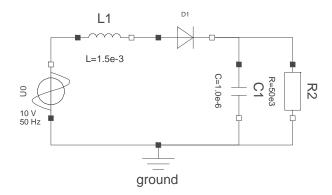
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- The simulation results look vastly different. Depending on the value of a fudge parameter that has no direct physical meaning, we got simulation trajectories that look significantly different.
- ▶ This simulation is garbage! It should never happen that the simulation trajectories are highly sensitive to a non-physical fudge parameter.
- ▶ The circuit is garbage! A real diode always has residual resistance values. If we build this circuit, its behavior will depend on how well we solder the diode into the circuit. Thus, we cannot expect to get any level of reproducibility out of this circuit. Two different specimen will behave very differently.

└─Variable Structure System

#### [H9.15] Mixed-mode Integration

#### Given the electrical circuit:



└Variable Structure System

#### [H9.15] Mixed-mode Integration II

We wish to simulate the circuit using the rkf45rt routine developed in homework problem [H9.1].

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- Since the diode is in series with an inductor, the causality on the switch equation is fixed, and consequently, we are dealing here with a variable structure system.
- We shall be using the mixed-mode integration approach to avoid the division by zero.
- Inline the inductor using backward Euler. Step-size control will now be limited to controlling the single continuous state variable defined by the voltage across the capacitor. The current through the inductor is now a discrete state variable. The step size of the backward Euler integrator will simply be in sync with that of the RKF4/5 algorithm.

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- ▶ Simulate the circuit across 0.05 seconds of simulated time.

└Variable Structure System

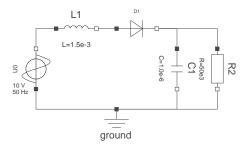
# [H9.15] Mixed-mode Integration III

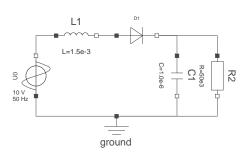
▶ Split the screen into two subgraphs, and plot in the top subgraph the voltages across the capacitor together from the current simulation run and from the more precise run of homework problem [H9.14], and on the bottom subgraph the step sizes used by the current simulation run and the more precise run of homework problem [H9.14].

└─Variable Structure System

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- What do you conclude?

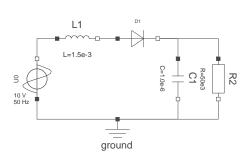
└─Variable Structure System





1: 
$$U_0 = V_0 \cdot \sin(\frac{2\pi t}{t_p})$$
  
2:  $u_L = L_1 \cdot di_0$   
3:  $i_0 = \operatorname{pre}(i_0) + h \cdot di_0$   
4:  $i_C = C_1 \cdot \frac{du_R}{dt}$   
5:  $u_R = R_2 \cdot i_R$   
6:  $U_0 = u_L + u_D + u_R$   
7:  $i_0 = i_C + i_R$   
8:  $u_D = m_0 \cdot s$   
9:  $i_0 = (1 - m_0) \cdot s$ 

## [H9.15] Mixed-mode Integration IV



1: 
$$U_0 = V_0 \cdot \sin(\frac{2\pi t}{t_p})$$
  
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 $m_0$  is a discrete state variable. It is *true*, when the diode is *blocking*.

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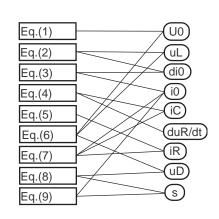
7: i_0 = i_C + i_R

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# [H9.15] Mixed-mode Integration V

1: 
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└─Variable Structure System

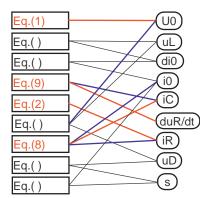
# [H9.15] Mixed-mode Integration VI

We causalize as much as we can:

└─Variable Structure System

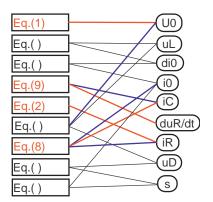
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1: 
$$U_0 = V_0 \cdot \sin(\frac{2\pi t}{t_p})$$

$$\begin{array}{cccc} P: & u_L & = & L_1 \cdot di_0 \\ P: & i_2 & = & \operatorname{pro}(i_2) + h \cdot di_2 \end{array}$$

?: 
$$u_L = L_1 \cdot di_0$$
  
?:  $i_0 = \operatorname{pre}(i_0) + h \cdot di_0$   
9:  $i_C = C_1 \cdot \frac{du_R}{dt}$   
2:  $u_R = R_2 \cdot i_R$ 

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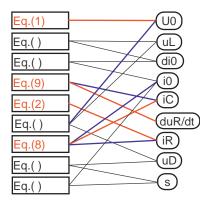
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We ended up with an algebraic loop in five equations and five unknowns. Luckily, the switch equation (variable s) is inside the algebraic loop.

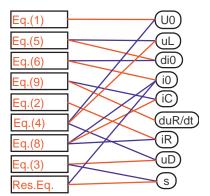
└─Variable Structure System

# [H9.15] Mixed-mode Integration VII

We choose s as our tearing variable:

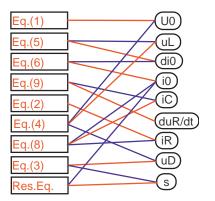
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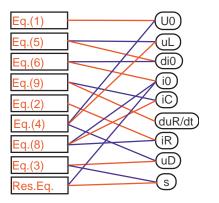
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5:  $di_0 = \frac{1}{L_1} \cdot u_L$   
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res.eq.:  $s = \frac{1}{1 - m_0} \cdot i_0$   
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We were able to causalize all of the remaining equations in this way.

# [H9.15] Mixed-mode Integration VIII

Substitution gives us the completely causal set of simulation equations:

1: 
$$U_0 = V_0 \cdot \sin(\frac{2\pi t}{t_p})$$
  
2:  $i_R = \frac{1}{R_2} \cdot u_R$   
3:  $s = \frac{L_1 \cdot \operatorname{pre}(i_0) + h \cdot (U_0 - u_R)}{L_1 \cdot (1 - m_0) + h \cdot m_0}$   
4:  $u_D = m_0 \cdot s$   
5:  $u_L = U_0 - u_D - u_R$   
6:  $di_0 = \frac{1}{L_1} \cdot u_L$   
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└─Variable Structure System

# [H9.15] Mixed-mode Integration VIII

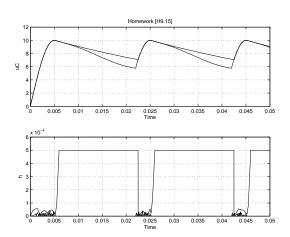
Substitution gives us the completely causal set of simulation equations:

1: 
$$U_0$$
 =  $V_0 \cdot \sin(\frac{2\pi t}{t_p})$   
2:  $i_R$  =  $\frac{1}{R_2} \cdot u_R$   
3:  $s$  =  $\frac{L_1 \cdot \operatorname{pre}(i_0) + h \cdot (U_0 - u_R)}{L_1 \cdot (1 - m_0) + h \cdot m_0}$   
4:  $u_D$  =  $m_0 \cdot s$   
5:  $u_L$  =  $U_0 - u_D - u_R$   
6:  $di_0$  =  $\frac{1}{L_1} \cdot u_L$   
7:  $i_0$  =  $\operatorname{pre}(i_0) + h \cdot di_0$   
8:  $i_C$  =  $i_0 - i_R$   
9:  $\frac{du_R}{dt}$  =  $\frac{1}{C_1} \cdot i_C$ 

If the diode operates in its blocking mode ( $m_0 = 1$ ), we unfortunately end up with h in the denominator of the equation computing s.

└─Variable Structure System

# [H9.15] Mixed-mode Integration IX



└─Variable Structure System

# [H9.15] Mixed-mode Integration X

▶ The new simulation executes very fast. There is no stiffness problem at all.

└Variable Structure System

# [H9.15] Mixed-mode Integration X

- ▶ The new simulation executes very fast. There is no stiffness problem at all.
- During the time, when the diode is blocking, the step size increases to the maximum value allowed, i.e., it increases to the communication interval.

# [H9.15] Mixed-mode Integration X

- The new simulation executes very fast. There is no stiffness problem at all.
- During the time, when the diode is blocking, the step size increases to the maximum value allowed, i.e., it increases to the communication interval.
- The simulation results look once again different. I would have needed to use values of  $R_{on}=10^{-10}\Omega$  and  $G_{off}=10^{-10}$  mho, in order to get simulation results out of the former model that look similar to those of the latter model. However, this would have been out of the question without using a stiff system solver. My notebook would have died of old age, before that simulation would have ended.

References

#### References

 Cellier, F.E. and M. Krebs (2007), "Analysis and Simulation of Variable Structure Systems Using Bond Graphs and Inline Integration," Proc. ICBGM07, 8<sup>th</sup> SCS Intl. Conf. on Bond Graph Modeling and Simulation, San Diego, California, pp. 29-34.